



BGU8H1

SiGe:C low-noise amplifier MMIC for LTE

Rev. 3 — 16 January 2017

Product data sheet

1. General description

The BGU8H1 is, also known as the LTE1001H, a Low-Noise Amplifier (LNA) for LTE receiver applications, available in a small plastic 6-pin extremely thin leadless package. The BGU8H1 requires one external matching inductor.

The BGU8H1 adapts itself to the changing environment resulting from co-habitation of different radio systems in modern cellular handsets. It has been designed for low power consumption and optimal performance. At low jamming power levels, it delivers 13 dB gain at a noise figure of 0.9 dB. During high-power levels, it temporarily increases its bias current to improve sensitivity.

The BGU8H1 is optimized for 2300 MHz to 2690 MHz.

2. Features and benefits

- Operating frequency from 2300 MHz to 2690 MHz
- Noise figure = 0.9 dB
- Gain = 13 dB
- High input 1 dB compression point of -1 dBm
- High in band $IP3_i$ of 8 dBm
- Supply voltage 1.5 V to 3.1 V
- Self-shielding package concept
- Integrated supply decoupling capacitor
- Optimized performance at a supply current of 5.0 mA
- Power-down mode current consumption < 1 μ A
- Integrated temperature stabilized bias for easy design
- Require only one input matching inductor
- Output DC decoupled
- ESD protection on all pins (HBM > 2 kV)
- Integrated matching for the output
- Available in a 6-pin leadless package 1.1 mm \times 0.7 mm \times 0.37 mm; 0.4 mm pitch: SOT1232
- 180 GHz transit frequency - SiGe:C technology
- Moisture sensitivity level 1



3. Applications

- LNA for LTE reception in smart phones
- Feature phones
- Tablet PCs
- RF front-end modules

4. Quick reference data

Table 1. Quick reference data

$f = 2350 \text{ MHz}$; $V_{CC} = 2.8 \text{ V}$; $V_{I(ENABLE)} \geq 0.8 \text{ V}$; $T_{amb} = 25 \text{ }^\circ\text{C}$; input matched to $50 \text{ } \Omega$ using a 3.3 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.5	-	3.1	V
I_{CC}	supply current		3.0	5.0	7.0	mA
G_p	power gain	[1]	-	13	-	dB
NF	noise figure	[1][2][3]	-	0.9	1.5	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	[1][3]	-7	-3	-	dBm
IP_{3i}	input third-order intercept point	[1][3]	1	6	-	dBm

[1] E-UTRA operating band 40 (2300 MHz to 2400 MHz).

[2] PCB losses are subtracted.

[3] Guaranteed by device design; not tested in production.

5. Ordering information

Table 2. Ordering information

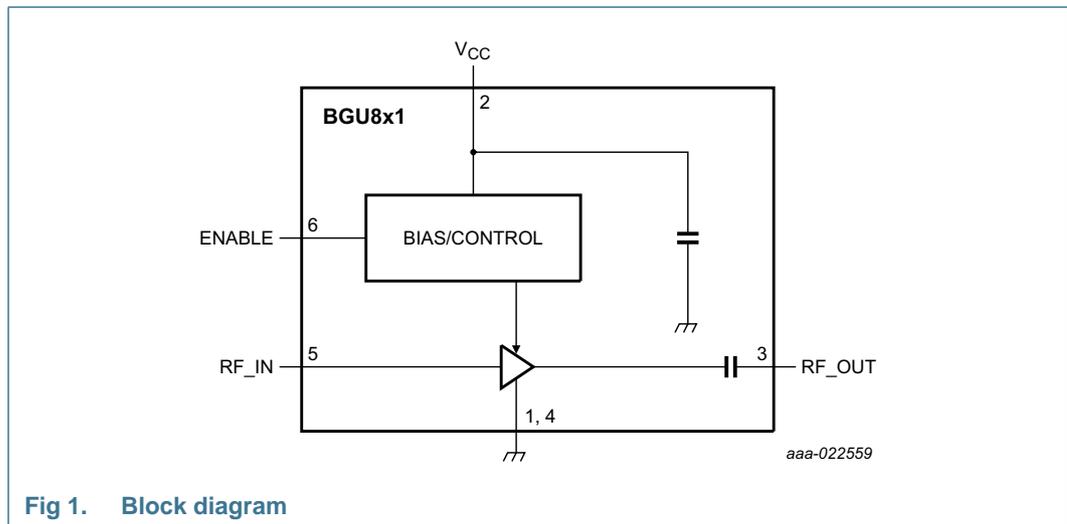
Type number	Package		Version
	Name	Description	
BGU8H1	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1.1 \times 0.7 \times 0.37 \text{ mm}$	SOT1232

6. Marking

Table 3. Marking codes

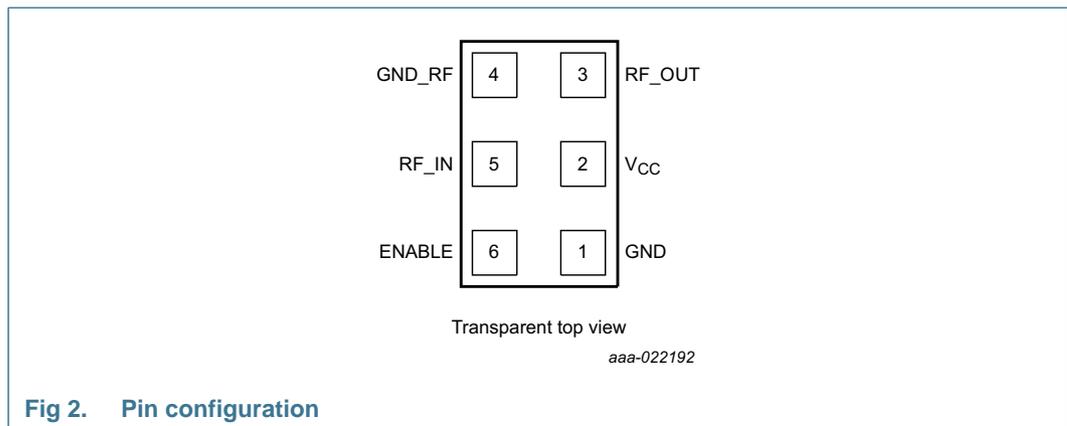
Type number	Marking code
BGU8H1	F

7. Block diagram



8. Pinning information

8.1 Pinning



8.2 Pin description

Table 4. Pin description

Symbol	Pin	Description
GND	1	ground
V _{CC}	2	supply voltage
RF_OUT	3	RF output
GND_RF	4	ground RF
RF_IN	5	RF input
ENABLE	6	enable

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Absolute maximum ratings are given as limiting values of stress conditions during operation, that must not be exceeded under the worst probable conditions.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled [1]	-0.5	+5.0	V
V _{I(ENABLE)}	input voltage on pin ENABLE	V _{I(ENABLE)} < V _{CC} + 0.6 V [1][2]	-0.5	+5.0	V
V _{I(RF_IN)}	input voltage on pin RF_IN	DC; V _{I(RF_IN)} < V _{CC} + 0.6 V [1][2]	-0.5	+5.0	V
V _{I(RF_OUT)}	input voltage on pin RF_OUT	DC; V _{I(RF_OUT)} < V _{CC} + 0.6 V [1][2][3]	-0.5	+5.0	V
P _i	input power	[1]	-	26	dBm
P _{tot}	total power dissipation	T _{sp} ≤ 130 °C	-	55	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM) according to ANSI/ESDA/JEDEC standard JS-001	-	±2	kV
		Charged Device Model (CDM) according to JEDEC standard JESD22-C101C	-	±1	kV

[1] Stressed with pulses of 1 s in duration. V_{CC} connected to a power supply of 2.8 V with 500 mA current limit.

[2] Warning: Due to internal ESD diode protection, to avoid excess current, the applied DC voltage must not exceed V_{CC} + 0.6 V or 5.0 V.

[3] The RF output is AC coupled through internal DC blocking capacitors.

10. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.5	-	3.1	V
T _{amb}	ambient temperature		-40	+25	+85	°C
V _{I(ENABLE)}	input voltage on pin ENABLE	OFF state	-	-	0.3	V
		ON state	0.8	-	-	V

11. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		225	K/W

12. Characteristics

Table 8. Characteristics at $V_{CC} = 1.8$ V

$2300 \text{ MHz} \leq f \leq 2690 \text{ MHz}$; $V_{CC} = 1.8 \text{ V}$; $V_{I(ENABLE)} \geq 0.8 \text{ V}$; $T_{amb} = 25^\circ\text{C}$; input matched to 50Ω using a 3.3 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	$V_{I(ENABLE)} \geq 0.8 \text{ V}$	2.8	4.8	6.8	mA
		$V_{I(ENABLE)} \leq 0.3 \text{ V}$	-	-	1	μA
G_p	power gain	$f = 2350 \text{ MHz}$ [1]	-	13.0	-	dB
		$f = 2500 \text{ MHz}$	10.5	12.5	14.5	dB
		$f = 2655 \text{ MHz}$ [2]	-	12.0	-	dB
RL_{in}	input return loss	$f = 2350 \text{ MHz}$ [1]	-	8	-	dB
		$f = 2655 \text{ MHz}$ [2]	-	8	-	dB
RL_{out}	output return loss	$f = 2350 \text{ MHz}$ [1]	-	20	-	dB
		$f = 2655 \text{ MHz}$ [2]	-	20	-	dB
ISL	isolation	$f = 2350 \text{ MHz}$ [1]	-	20	-	dB
		$f = 2655 \text{ MHz}$ [2]	-	20	-	dB
NF	noise figure	$f = 2350 \text{ MHz}$ [1][3][4]	-	0.9	1.5	dB
		$f = 2655 \text{ MHz}$ [2][3]	-	1.1	-	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	$f = 2350 \text{ MHz}$ [1][4]	-12	-8	-	dBm
		$f = 2655 \text{ MHz}$ [2]	-	-7	-	dBm
IP _{3i}	input third-order intercept point	$f = 2350 \text{ MHz}$ [1][4]	-3	+2	-	dBm
		$f = 2655 \text{ MHz}$ [2]	-	5	-	dBm
K	Rollett stability factor		1	-	-	-
t_{on}	turn-on time	time from $V_{I(ENABLE)}$ ON to 90 % of the gain	-	-	4	μs
t_{off}	turn-off time	time from $V_{I(ENABLE)}$ OFF to 10 % of the gain	-	-	1	μs

[1] E-UTRA operating band 40 (2300 MHz to 2400 MHz).

[2] E-UTRA operating band 7 (2620 MHz to 2690 MHz).

[3] PCB losses are subtracted.

[4] Guaranteed by device design; not tested in production.

Table 9. Characteristics at $V_{CC} = 2.8$ V

$2300 \text{ MHz} \leq f \leq 2690 \text{ MHz}$; $V_{CC} = 2.8 \text{ V}$; $V_{I(ENABLE)} \geq 0.8 \text{ V}$; $T_{amb} = 25 \text{ }^\circ\text{C}$; input matched to $50 \text{ } \Omega$ using a 3.3 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	$V_{I(ENABLE)} \geq 0.8 \text{ V}$	3.0	5.0	7.0	mA
		$V_{I(ENABLE)} \leq 0.3 \text{ V}$	-	-	1	μA
G_p	power gain	$f = 2350 \text{ MHz}$ [1]	-	13	-	dB
		$f = 2500 \text{ MHz}$	10.8	12.8	14.8	dB
		$f = 2655 \text{ MHz}$ [2]	-	12.5	-	dB
RL_{in}	input return loss	$f = 2350 \text{ MHz}$ [1]	-	9	-	dB
		$f = 2655 \text{ MHz}$ [2]	-	9	-	dB
RL_{out}	output return loss	$f = 2350 \text{ MHz}$ [1]	-	20	-	dB
		$f = 2655 \text{ MHz}$ [2]	-	20	-	dB
ISL	isolation	$f = 2350 \text{ MHz}$ [1]	-	22	-	dB
		$f = 2655 \text{ MHz}$ [2]	-	22	-	dB
NF	noise figure	$f = 2350 \text{ MHz}$ [1][3][4]	-	0.9	1.5	dB
		$f = 2655 \text{ MHz}$ [2][3]	-	1.0	-	dB
$P_{i(1dB)}$	input power at 1 dB gain compression	$f = 2350 \text{ MHz}$ [1][4]	-7	-3	-	dBm
		$f = 2655 \text{ MHz}$ [2]	-	-1	-	dBm
IP3 _i	input third-order intercept point	$f = 2350 \text{ MHz}$ [1][4]	1	6	-	dBm
		$f = 2655 \text{ MHz}$ [2]	-	8	-	dBm
K	Rollett stability factor		1	-	-	-
t_{on}	turn-on time	time from $V_{I(ENABLE)}$ ON to 90 % of the gain	-	-	4	μs
t_{off}	turn-off time	time from $V_{I(ENABLE)}$ OFF to 10 % of the gain	-	-	1	μs

[1] E-UTRA operating band 40 (2300 MHz to 2400 MHz).

[2] E-UTRA operating band 7 (2620 MHz to 2690 MHz).

[3] PCB losses are subtracted.

[4] Guaranteed by device design; not tested in production.

13. Package outline

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1.1 x 0.7 x 0.37 mm

SOT1232

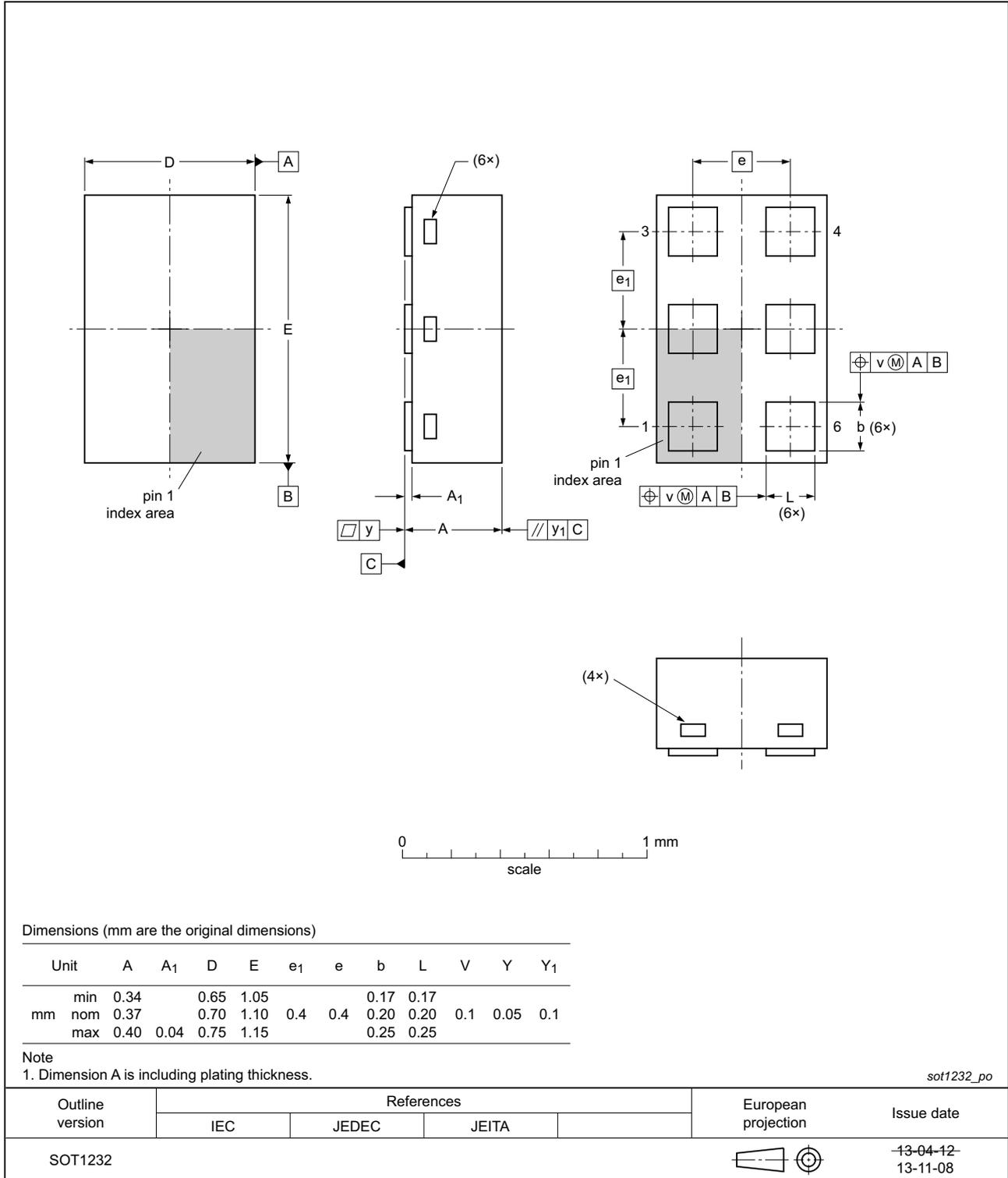


Fig 3. Package outline SOT1232 (XSON6)

14. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

15. Abbreviations

Table 10. Abbreviations

Acronym	Description
ESD	ElectroStatic Discharge
E-UTRA	Evolved UMTS Terrestrial Radio Access
HBM	Human Body Model
LNA	Low-Noise Amplifier
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
PCB	Printed-Circuit Board
SiGe:C	Silicon Germanium Carbon

16. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU8H1 v.3	20170116	Product data sheet	-	BGU8H1 v.2
Modifications:	<ul style="list-style-type: none"> Section 1: added LTE1001H according to our new naming convention 			
BGU8H1 v.2	20160428	Product data sheet	-	BGU8H1 v.1
Modifications:	<ul style="list-style-type: none"> Table 5: updated value input power; added Table note [1] Table 8: updated G_p power gain with $f = 2500$ MHz; added Table note [4] Table 9: updated G_p power gain with $f = 2500$ MHz; added Table note [4] 			
BGU8H1 v.1	20140603	Product data sheet	-	-

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17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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